

5,827,773

117/092

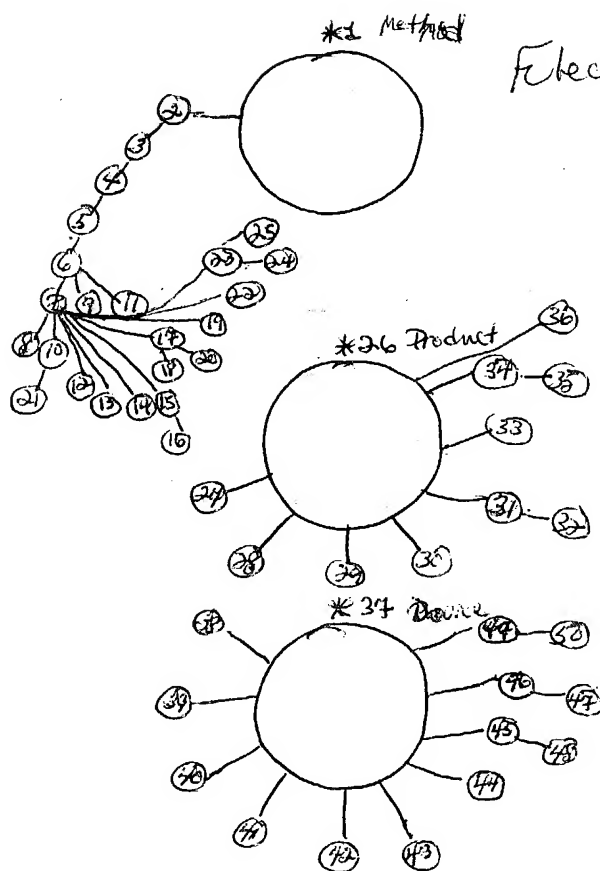
10/602,186

103 Rej. Claims 1-6, 8 and 10

Examiner's Notes

David C. Ripme
Tel# (360) 834-8754
(360) 817-8505

Allowable Subject Matter:
Objected To Claims 7, 9 and 11-25



Electro Ceramics (Claims 1-25)

Motivation: In order to have an annealing process that could be desired & controlled w/ the grain orientation of crystals in a significant region of S.C. film) to have a significant region of S.C. film with a controlled, single crystal orientation to enhance the predictability of device performance.

8.08 1) [51-25 are]

2) [A mtd for forming a SC film single crystal domains.]

MTD
I 3) [117]

4) [92]

5) [526-36 are]

6) [A semiconductor structure w/ lateral single crystal]

7) [428]

Prod
II 8) [14]

8.09 1) [537-50 are]

2) [A single-crystal thin-film transistor (TFT).]

App
III 3) [438]

4) [14]

I → II

I → III

II → III